

TS2026 Dual-Channel Power Distribution Switch

SOP-8	
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Pin assignment:1. ENA5. OUTB2. FLGA6. GND3. FLGB7. IN4. ENB8. OUTA

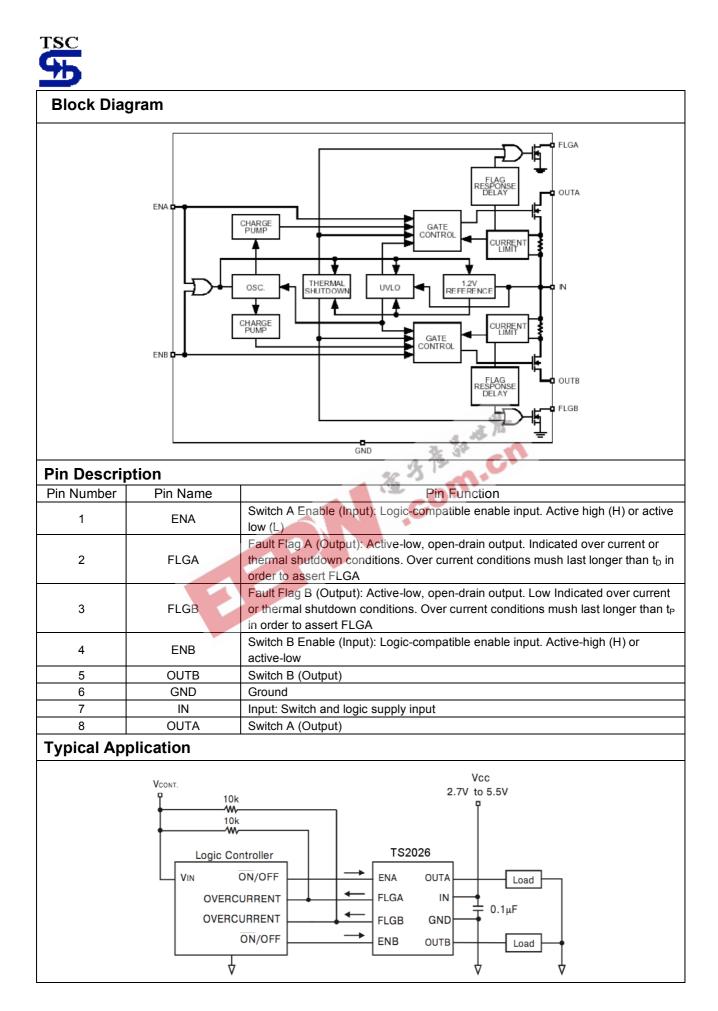
140mΩ max. on-resistance per channel2.7V to 5.5V operating rangeUnder voltage lockout

General Description

The TS2026 is high-side MOSFET switches optimized for general-purpose power distribution requiring circuit protection. The TS2026 are internally current limited and have thermal shutdown that protects the device and load. When a thermal shutdown fault occurs, the output is latched off until the faulty load is removed. Removing that load or toggling the enable input will reset the device output. Both device employ soft-start circuitry that minimized inrush current in application where highly capacitive loads are employed. A fault status output flag is asserted during over current and thermal shutdown conditions. Transient faults are internally filtered.

Features

\diamond 140m Ω max. on-resistance per channel			∻	♦ Under voltage lockout					
♦ 2.7V to 5.5V operating range				\diamond	a desta de la construcción de				
 500mA min. continuous current per channel Short-circuit protection with thermal shutdown 				 ♦ Logic-compatible inputs ♦ Soft-start circuit 					
									♦ Thermal isolated channels.
♦ Fault status flag with 3ms filter eliminates false									
	assertions.			Ų					
Orde	ering Info	ormation							
Р	art No.	Operating Temp. (Ambient)	ackage						
TS	2026CS	-20 ~ +85 °C	SOP-8						
۸nn	lications								
 USB peripherals General purpose power switching 				 ♦ Notebook PCs ♦ PDAs 					
 General purpose power switching ACPI power distribution 				∽ ∻	PDAs PC card hot swap				
	•			Ŷ	i o calo not swap				
Abs	olute Ma	ximum Rating							
Supply Voltage			V _{IN}		+6	V			
Fault Flag Voltage			V _{FLG}		+6	V			
Fault Flag Current		I _{FLG}		25	mA				
Output Voltage		Vout		+6	°C				
Output Current		I _{OUT}		Internal Limited					
Enable input			I _{EN}		-0.3 ~ +3	V			
-	Storage Temperature				-65 ~ +150	°C			





$VIn=5V$, $I_A = 25$ C, bold values	s indicate -40	$0^{\circ}C \le T_{A} \le 85^{\circ}C$ unless noted				
Parameter	Symbol	Condition	Min.	Тур.	Max.	Units
Supply Current		TS2026-L, V _{ENA} =V _{ENB} ≥2.4V (switch off), OUT = open		0.75	5	А
Supply Current	I _{DD}	TS2026-H, V _{ENA} =V _{ENB} ≤0.8V (switch on), OUT = open		100	160	А
Enable Input threshold	V _{EN}	Low-to-high transition		1.7	2.4	V
		High-to-low transition	0.8	1.455		V
Enable Input Hysteresis				250		mV
Enable Input Current	- Iev	V _{ENA} = 0V to 5.5V	-1	0.01	1	A
Enable Input Capacitance	I _{EN}			1		pF
Switch Registered Note 4	R _{DS(ON)}	V _{IN} = 5V, I _{OUT} = 500mA		90	140	mΩ
Switch Resistance Note 4		V _{IN} = 3.3V, I _{OUT} = 500mA		100	160	mΩ
Output Leakage Current		TS2026-H, V _{ENX} ≤0.8V TS2026-L, V _{ENX} ≥2.4V			10	A
Output Turn-on Delay	$\begin{array}{c c} \mbox{Furn-on Delay} & t_{ON} & R_L = 10 \Omega, \\ \mbox{see "Tim} \end{array}$		-	1.3	5	mS
Output Turn-on Rise Time	t _R	R _L =10Ω, C _L =1F, see "Timing Diagrams"	25	1.15	4.9	mS
Output Turn-off Delay	t _{OFF}	$R_L=10\Omega$, $C_L=1F$, see "Timing Diagrams"	N	35	100	S
Output Turn-off Fall Time	t⊧	R _L =10Ω, C _L =1F, see "Timing Diagrams"		32	100	S
Short-Circuit Output Current	LIMIT	V _{OUT} = 0V, enable in to short-circuit	0.5	0.9	1.25	A
Current –Limit Threshold		Ramped load applied to output		1.0	1.25	А
Short-Circuit Response Time		V _{OUT} = 0V to I _{OUT} = I _{LIMIT} (short applied to output)		20		S
Over current Flag Response	t _D	V _{IN} =5V, apply V _{OUT} =0V Until FLG low	1.5	3	7	mS
Delay		V _{IN} =3.3V, apply V _{OUT} =0V Until FLG low	TBD	3		mS
Under voltage Lockout		V _{IN} rising	2.2	2.4	2.7	V
Threshold		V _{IN} falling	2.0	2.15	2.5	V
Error Elon Output Desister		I _L =10mA, V _{IN} =5V		10	25	Ω
Error Flag Output Resistance		I _L =10mA, V _{IN} =3.3V		15	40	Ω
Error Flag Off Current		V _{FLAG} =5V			10	А
		T _J increasing, each switch		140		°C
Over temperature Threshold		T _J decreasing, each switch		120		°C
Note 5		T _J increasing, both switch		160		°C
		T _J decreasing, both switch		150		°C

Note 1. Exceeding the absolute maximum rating may damage the device.

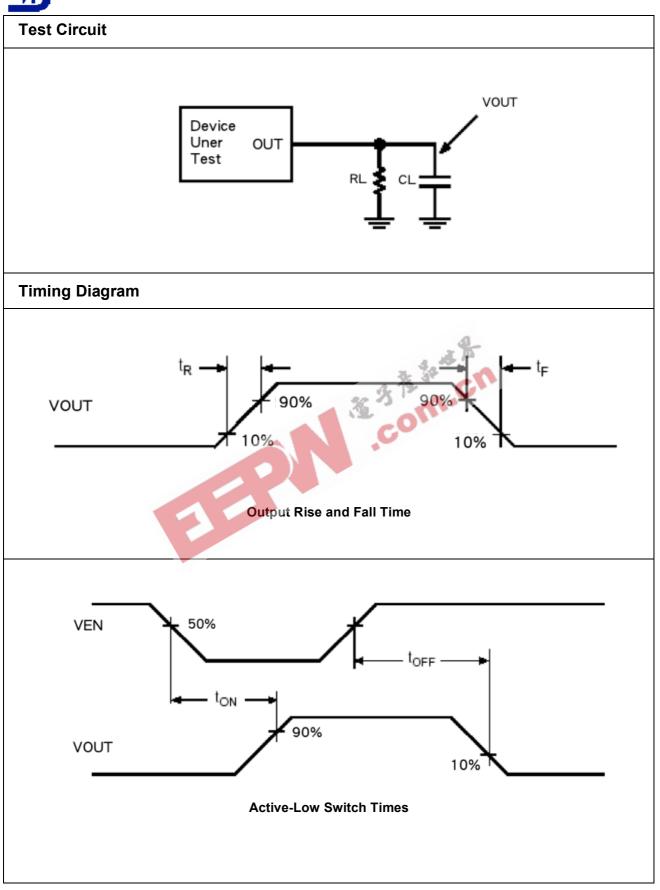
Note 2. The device is not guaranteed to function outside its operating rating.

Note 3. Devices are ESD sensitive. Handing precautions recommended.

Note 4. For maintenance $R_{DS} \le 140 m\Omega$ assembly to make gold conductors in diameter 50m.

Note 5. If there is a fault on one channel, that channel will shut down when the die reaches approximately $140 \,^{\circ}$ C. If the die reaches approximately $160 \,^{\circ}$ C, both channels will shut down, even if neither channel is in current limit.







Function Description

Input and Output

IN is the power supply connection to the logic circuitry and the drain of the output MOSFET. OUT is the source of the output MOSFET. In a typical circuit, current flows from IN to OUT toward the load. If Vout is greater than VIN. current will flow from OUT to IN, since the switch is bidirectional when enabled. The output MOSFET and driver circuitry are also designed to allow the MOSFET source to be externally forced to a higher voltage than the drain (V_{OUT} > V_{IN}) when the switch is disabled. In this situation, the TS2026 prevents undesirable current flow from OUT to IN.

Thermal Shutdown

Thermal shutdown is employed to protect the device from damage should the die temperature exceed safe margins due mainly to short circuit faults. Each channel employs its own thermal sensor. Thermal shutdown shuts off the output MOSFET and asserts the FLG output if the die temperature reaches 140 °C and the overheated channel is in current limit. The over channel will be shut off. Upon determining a thermal shutdown condition. The TS2026 will automatically reset its output when the die temperature cools down to 120 °C . The TS2026 output and FLG signal will continue to cycle on and off until the device is disabled or the fault is removed. Figure 1. Depicts typical timing. Depending on PCB layout, package, ambient temperature, etc., it may take several hundred milliseconds from the incidence of the fault to the output MOSFET being shut off. This time will be shortest in the case of dead short on the output.

Power Dissipation

The device's junction temperature depends on several factors such as the load. PCB layout, ambient temperature and package type. Equations that can be used to calculate power dissipation of each channel and junction temperature are found below.

 $P_D = R_{DS(ON)} x I_{OUT}^2$

connels. To Total power dissipation of the device will be the summation of PD for both channels. To relate this to junction temperature, the following equation can be used:

$$T_{J} = P_{D} \times \theta_{JA} + T_{A}$$

Where:

- T_{J} = junction temperature
- T_A = ambient temperature
- θ_{JA} = is the thermal resistance of the package

Current Sensing and Limiting

The current-limit threshold is preset internally. The preset level prevents damage to the device and external load but still allows a minimum current of 500mA to be delivered to the load. The current-limit circuit senses a portion of the output MOSFET switch current. The current-sense resistor shown in the block diagram is virtual and has no voltage drop. The reaction to an over current condition varies with three scenarios.

Switch Enable into Short-Circuit

If a switch is enabled into a heavy load or short-circuit, the switch immediately enters into a constant-current mode, reducing the output voltage. The FLG signal is asserted indicating an over current condition.

Switch Enable Applied to Enabled Output

When a heavy load or short-circuit is applied to an enabled switch, a large transient current may flow until the current limit circuitry responds. Once this occurs the device limits current to less than the short circuit current limit specification.

Current-Limit Response-Ramped Load

The TS2026 current-limit profile exhibits a small fold back effect of about 200mA. Once this current-limit threshold is exceeded the device switches into a constant current mode. It is important to note that the device will supply current up to the current-limit threshold

Fault Flag

The FLG signal is an N-channel open-drain MOSFET output. FLG is asserted (active-low) when either an over current or thermal shutdown condition occurs. In the case of and over current condition, FLG will be asserted only after the flag response delay time, t_D, has elapsed. This ensured that FLG is asserted only upon valid over current conditions and that erroneous error reporting is eliminated. For example, false over current condition can occur during hot plug event when a highly capacitive load is connected and causes a high transient inrush current that exceeds the current-limit threshold for up to 1ms. The FLG response delay time t_D is typically 3ms.

Undervoltage Lockout

Undervolrage lockout (UVLO) prevents the output MOSFET from turning on until VIN exceeds approximately 2.5V. Undervoltage detection function only when the switch is enabled.

